

N-CHANNEL MOSFET

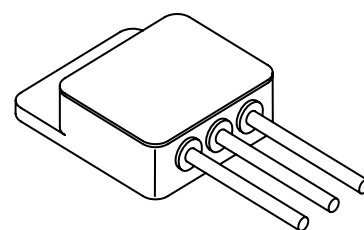
DEVICES

APT6017WVR
POWER MOS V[®]
600V 31.5A 0.170Ω

LEVELS
TX, TXV, S
CUSTOM SCREENS
AVAILABLE

ABSOLUTE MAXIMUM RATINGS ($T_C = +25^\circ\text{C}$ unless otherwise noted)

Parameters / Test Conditions	Symbol	Value	Unit
Drain – Source Voltage	V_{DS}	600	Vdc
Gate – Source Voltage	V_{GS}	± 30	Vdc
Continuous Drain Current $T_C = +25^\circ\text{C}$	I_{D1}	31.5	Adc
Max. Power Dissipation $T_C = +25^\circ\text{C}$	P_{tl}	450 ⁽¹⁾	W
Drain to Source On State Resistance	$R_{ds(on)}$	0.170 ⁽²⁾	Ω
Operating & Storage Temperature	T_{op}, T_{stg}	-55 to +150	$^\circ\text{C}$
Lead temperature: 0.063" from Case for 10 Se.	T_L	300	$^\circ\text{C}$
Avalanche Current ⁽³⁾ (Repetitive/ Non-repetitive)	I_{AR}	31.5	Adc
	E_{AR}	50	mJ
	E_{AS}	2500	mJ

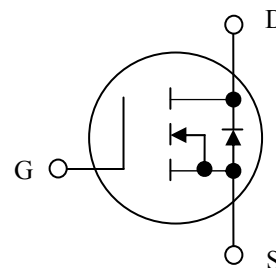


TO-267

Note: (1) Derated Linearly by 3.6 W/ $^\circ\text{C}$ for $T_C > +25^\circ\text{C}$
(2) $V_{GS} = 10\text{Vdc}$, $I_D = 15.75\text{A}$
(3) Repetitive Rating: Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS ($T_A = +25^\circ\text{C}$, unless otherwise noted)

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Drain-Source Breakdown Voltage $V_{GS} = 0\text{V}$, $I_D = 1\text{mAdc}$	$V_{(BR)DSS}$	600		Vdc
Gate-Source Voltage (Threshold) $V_{DS} \geq V_{GS}$, $I_D = 0.25\text{mA}$	$V_{GS(th)1}$	2.0	4.0	Vdc
Gate Current $V_{GS} = \pm 30\text{V}$, $V_{DS} = 0\text{V}$ $V_{GS} = \pm 20\text{V}$, $V_{DS} = 0\text{V}$, $T_j = +125^\circ\text{C}$	I_{GSS1} I_{GSS2}		± 100 ± 200	nAdc
Drain Current $V_{GS} = 0\text{V}$, $V_{DS} = 600\text{V}$ $V_{GS} = 0\text{V}$, $V_{DS} = 480\text{V}$, $T_j = +125^\circ\text{C}$	I_{DSS1} I_{DSS2}		25 0.25	μAdc mAdc
Static Drain-Source On-State Resistance $V_{GS} = 10\text{V}$, $I_D = 15.75\text{A}$ pulsed	$r_{DS(on)}$		0.170	Ω
Diode Forward Voltage $V_{GS} = 0\text{V}$, $I_D = 31.5\text{A}$ pulsed	V_{SD}		1.3	Vdc



DYNAMIC CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Capacitance:				
Input capacitance $V_{GS} = 0V$	C_{iss}		9000	pF
Output Capacitance $V_{DS} = 25V$	C_{oss}		1260	
Reverse Transfer Capacitance $f = 1 \text{ MHz}$	C_{rss}		480	
Gate Charge:				
On-State Gate Charge $V_{GS} = 10V, I_D = 31.5A$	$Q_{g(on)}$		475	nC
Gate to Source Charge $V_{DS} = 300V$	Q_{gs}		70	
Gate to Drain Charge	Q_{gd}		190	

SWITCHING CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Switching time tests:				
Turn-on delay time $I_D = 31.5A, V_{GS} = 15Vdc,$	$t_{d(on)}$		30	ns
Rinse time Gate drive impedance = $0.6\Omega,$	t_r		26	
Turn-off delay time $V_{DD} = 300Vdc$	$t_{d(off)}$		70	
Fall time	t_f		10	
Diode Reverse Recovery Time $di/dt \leq 100A/\mu s, V_{DD} \leq 30V, I_F = 31.5A$	t_{rr}		690	ns
Diode Reverse Recovery Charge $di/dt \leq 100A/\mu s, V_{DD} \leq 30V, I_F = 31.5A$	Q_{rr}		15.9	uC

THERMAL CHARACTERISTICS

Parameters / Test Conditions	Symbol	Min.	Max.	Unit
Junction to Case	$R_{\theta JC}$		0.28	$^{\circ}C/W$
Junction to Ambient	$R_{\theta JA}$		40	$^{\circ}C/W$

GRAPHS

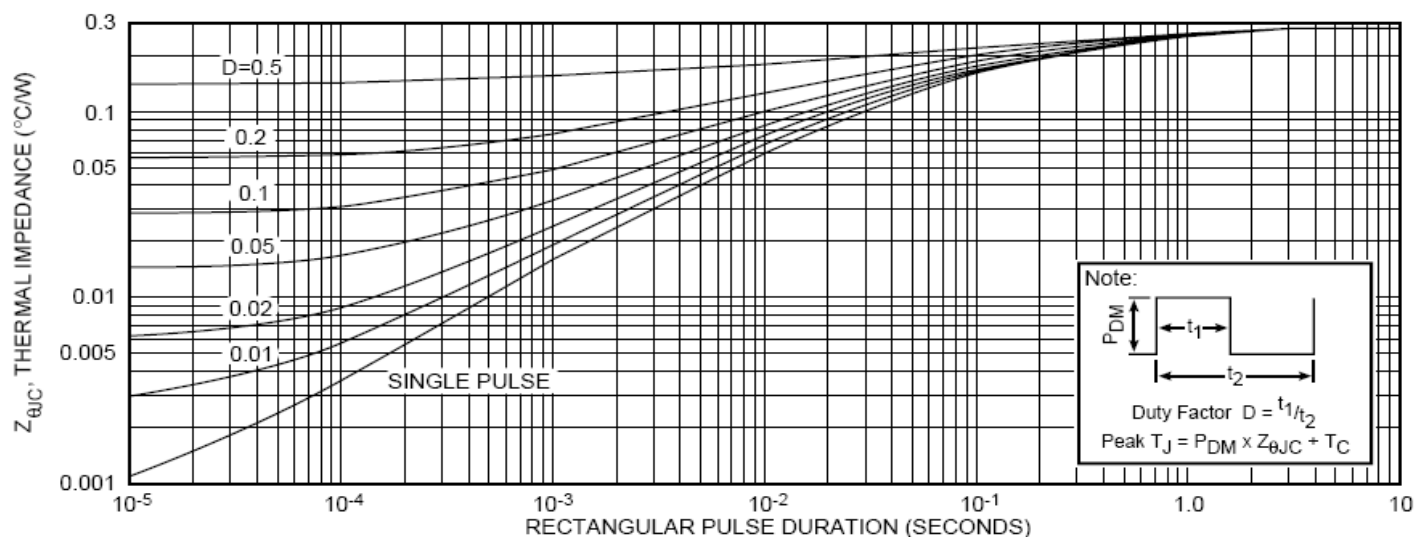


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

APT6017WVR

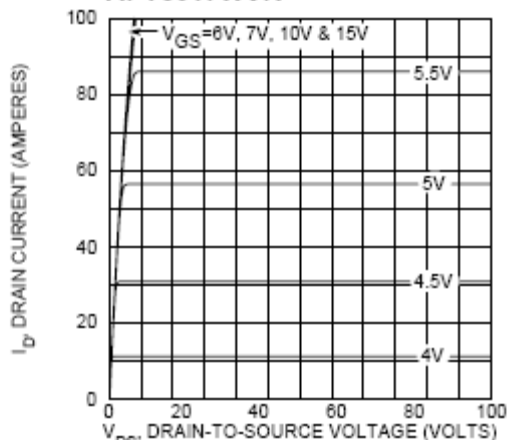


FIGURE 2. TYPICAL OUTPUT CHARACTERISTICS

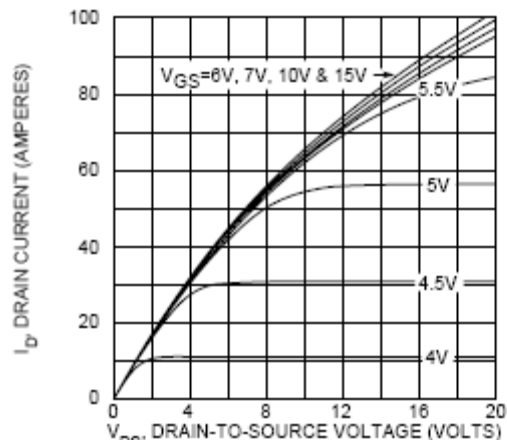


FIGURE 3. TYPICAL OUTPUT CHARACTERISTICS

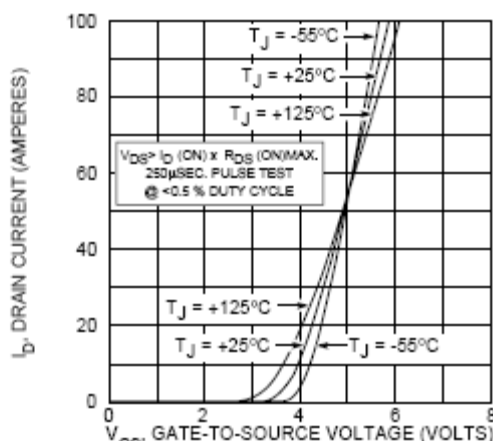


FIGURE 4. TYPICAL TRANSFER CHARACTERISTICS

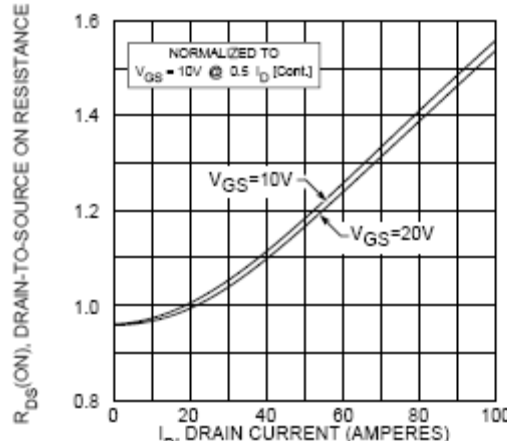


FIGURE 5. $R_{DS(ON)}$ vs DRAIN CURRENT

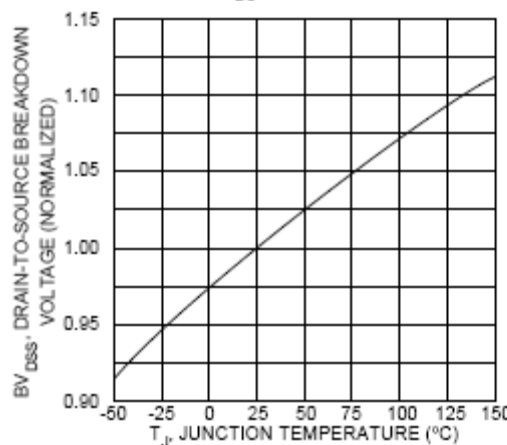
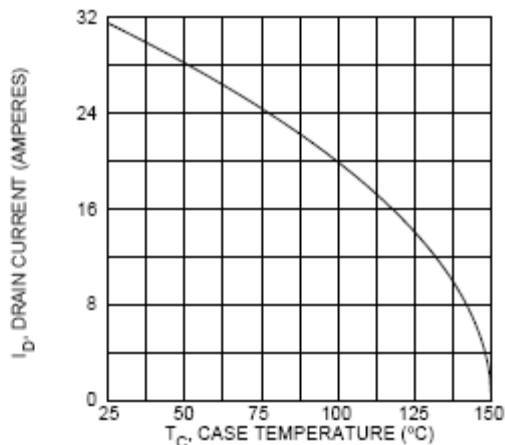


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

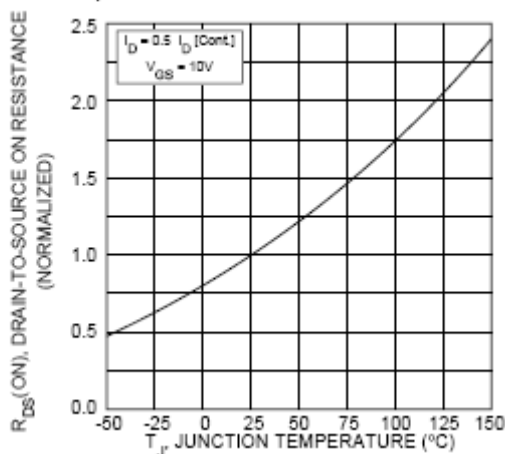


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

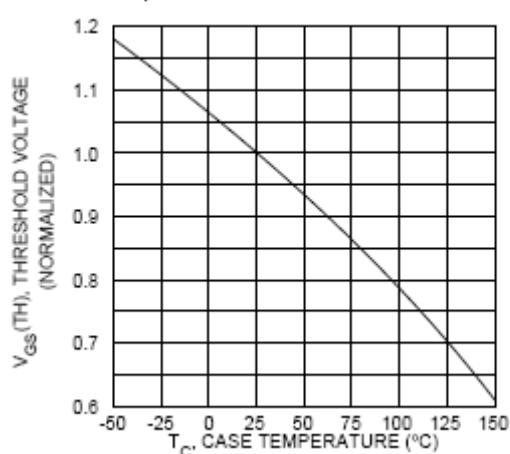


FIGURE 8, ON-RESISTANCE vs. TEMPERATURE

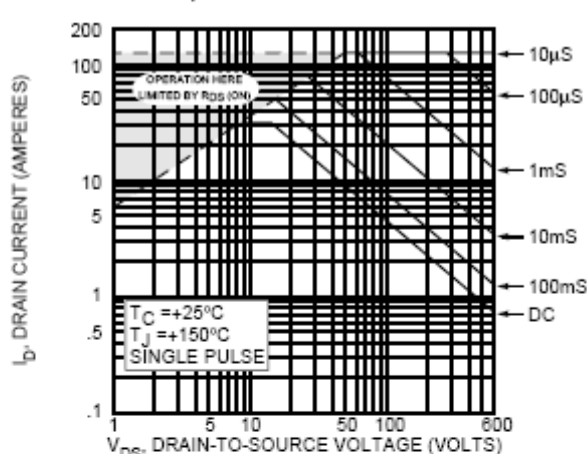


FIGURE 10, MAXIMUM SAFE OPERATING AREA

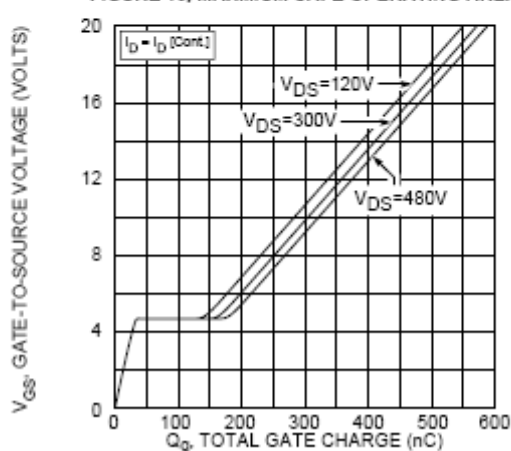


FIGURE 12, GATE CHARGES vs GATE-TO-SOURCE VOLTAGE

FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

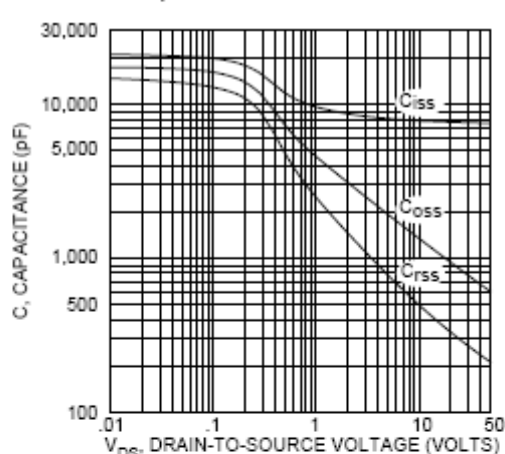


FIGURE 11, TYPICAL CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

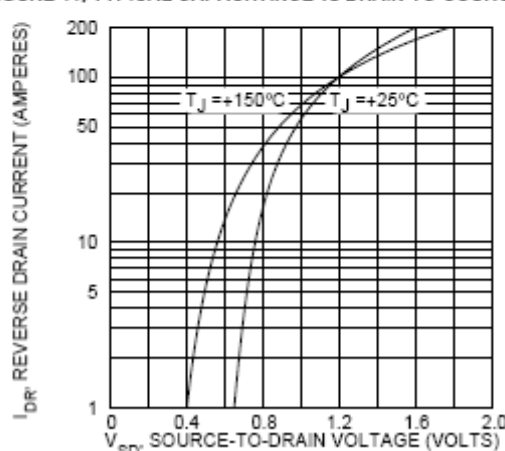
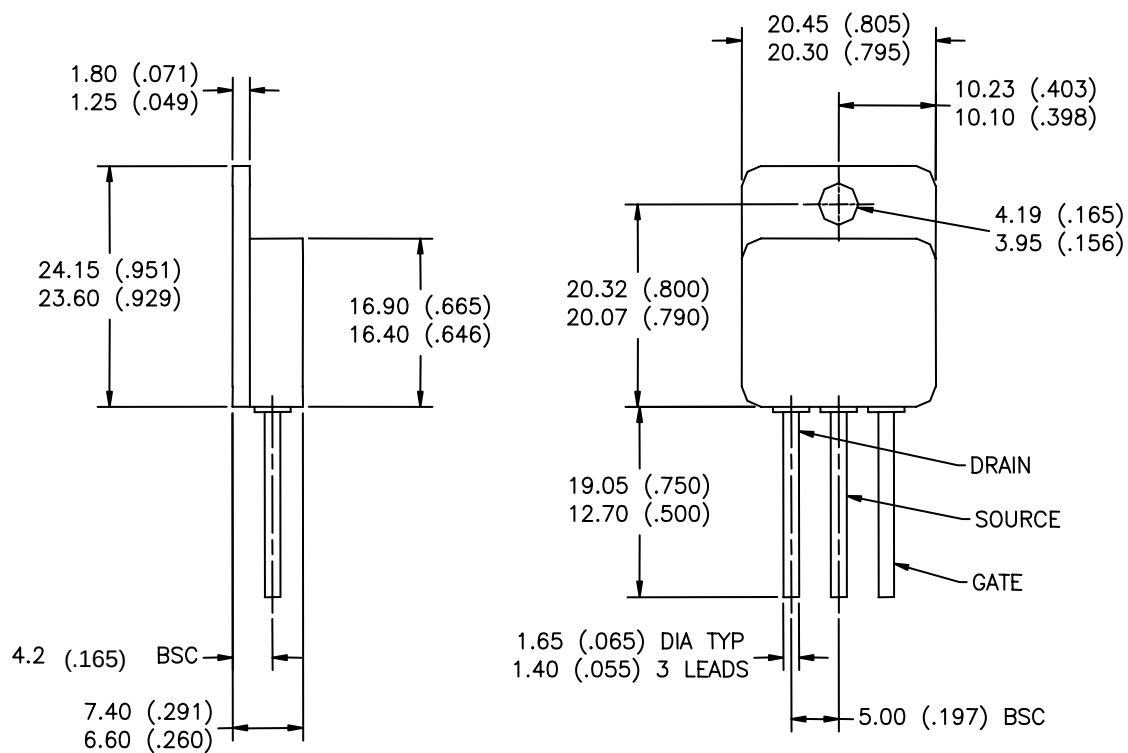


FIGURE 13, TYPICAL SOURCE-DRAIN DIODE FORWARD VOLTAGE

PACKAGE DIMENSIONS



DIMENSIONS IN MILLIMETERS AND (INCHES)